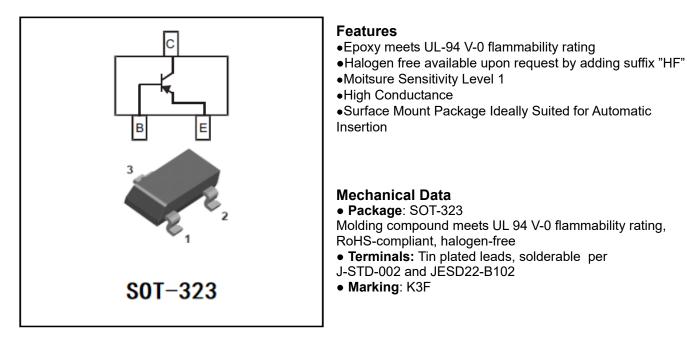




PNP Transistor



■ Maximum Ratings (Ta=25 °C unless otherwise noted)

Item	Symbol	Unit	Value
Collector-Base Voltage	V _{CBO}	V	-60
Collector-Emitter Voltage	V _{CEO}	V	-60
Emitter-Base Voltage	V _{EBO}	V	-5
Collector Current	Ι _C	mA	-600
Collector Power Dissipation	Pc	mW	200
Operation Junction Temperature	Tj	°C	150
Storage Temperature	T _{stg}	°C	-55 to +150

■ Electrical Characteristics (Ta=25°C unless otherwise noted)

Item	Symbol	Unit	Conditions	Min	Тур	Мах
Collector-base breakdown voltage	V _{CBO}	V	IC=-10uA,IE=0	-60		
Collector-emitter breakdown voltage	$V_{CEO^{\star}}$	V	IC =-10mA,IB=0	-60		
Emitter-base breakdown voltage	V _{EBO}	V	IE=-10μΑ,IC=0	-5		
Collector-emitter cut-off current	I _{CEO}	nA	VCE=-35V, IB=0			-50
Collector-base cut-off current	I _{CBO}	nA	VCB=-50V, IE =0			-10
Emitter-base cut-off current	I _{EBO}	nA	VEB=-3 V, IC =0			-10
DC current gain	h _{FE}		VCE=-10V,IC=-1mA	100		
	h _{FE}		VCE=-10V,IC=-150mA	100		300
Collector-emitter saturation voltage	V _{CE(sat)}	V	IC=-500mA,IB=-50mA			-1.6
Base-emitter saturation voltage	$V_{BE(sat)}$	V	IC=-500mA,IB=-50mA			-2.6
Transition frequency	f⊤	MHz	VCE=-20V,IC=-50mA,f=100MHz	200		
Delay time	td	ns				10
Rise time	tr	ns	VCC=-30V, IC=-150mA,IB1=-15mA			40
Storage time	ts	ns	VCC=-30V,IC=-150mA,			80
Fall time	tf	ns	IB1=IB2=-15mA			30

Ordering Information (Example)

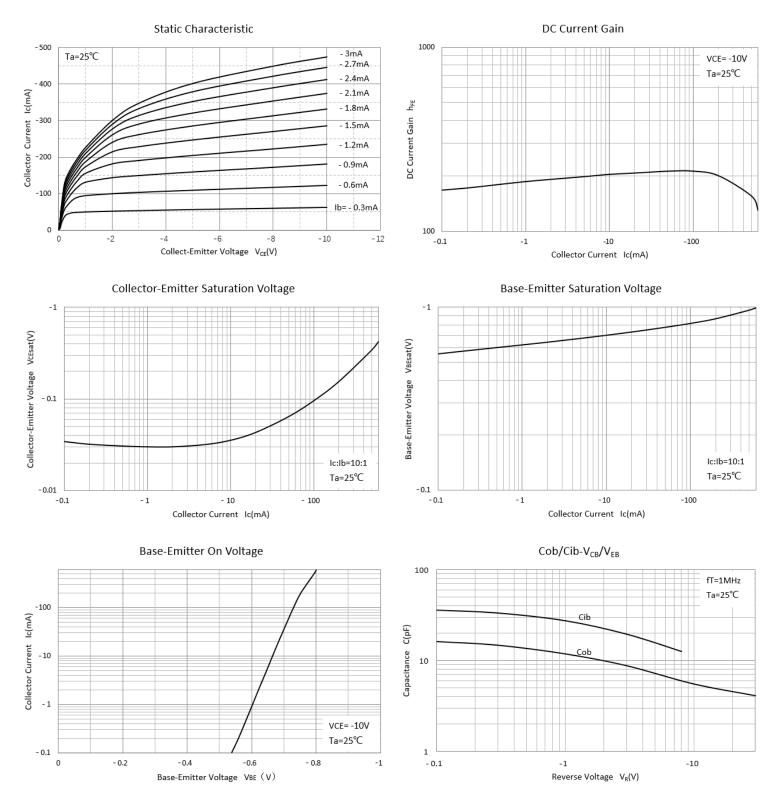
Prefered P/N	Packing Code	Unit Weight(G)	Minimum Package(Pcs)	Inner Box Quantity(Pcs)	Outer Carton Quantity(Pcs)	Delivery Mode
MMST2907A	F2	Approximate 0.005	3000	30000	120000	7" reel

2/5





Characteristics (Typical)

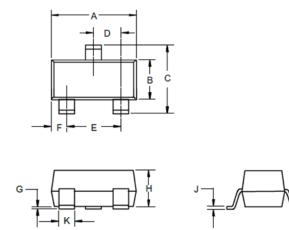


3/5



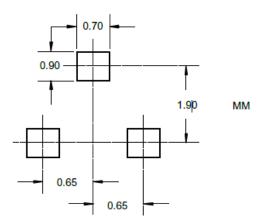


SOT-323 Package Outline Dimensions



DIMENSIONS						
	INCHES		ММ			
DIM	MIN	MAX	MIN	MAX	NOTE	
Α	.071	.087	1.80	2.20		
В	.045	.053	1.15	1.35		
С	.083	.096	2.10	2.45		
D	.026 Nominal		0.65Nominal			
E	.047	.055	1.20	1.40		
F	.012	.016	.30	.40		
G	.000	.004	.000	.100		
Н	.035	.039	.90	1.00		
J	.004	.010	.100	.250		
K	.006	.016	.15	.40		

SOT-323 Soldering Footprint





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 NTE92
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 2N6728
 2SA1419T-TD-H
 2SA2126-E
 2SB1204S-TL-E
 2SC2712S-GR,LF
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